

## Electronic Supporting Information

### **Computational Screening of Single Atom Catalysts Supported by VS<sub>2</sub> Monolayer for Electrocatalytic Oxygen Reduction/Evolution Reactions**

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**Table S1.** The computed  $\Delta G$  values of each elementary step in ORR on Ni@VS<sub>2</sub> catalyst with and without DFT+U approach.

<b>Elemental Step</b>	<b>without DFT+U</b>	<b>with DFT+U</b>
$O_2 \rightarrow OOH^*$	-0.78	-0.71
$OOH^* \rightarrow O^*$	-1.54	-1.57
$O^* \rightarrow OH^*$	-1.45	-1.52
$OH^* \rightarrow H_2O$	-1.16	-1.12

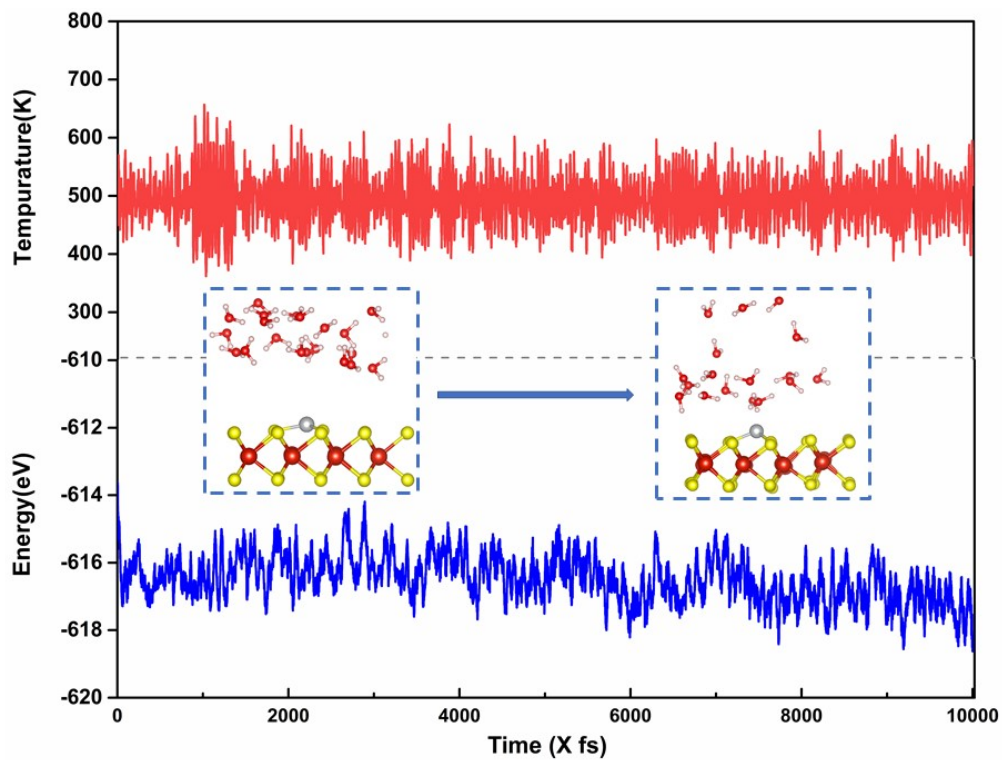
**Table S2.** The computed free adsorption energies ( $\Delta G$ , eV) of oxygenated intermediates on various TM@VS<sub>2</sub> materials.

TM	$\Delta G_{\text{OH}^*}$	$\Delta G_{\text{O}^*}$	$\Delta G_{\text{OOH}^*}$
Ti	-1.50	-0.65	2.15
V	-1.50	-1.28	1.90
Cr	-0.86	-0.59	2.61
Mn	-0.30	0.73	3.10
Fe	0.11	1.44	3.51
Co	0.44	1.65	3.67
Ni	1.16	2.60	4.14
Cu	0.87	3.11	3.99
Zr	-1.94	-1.02	1.84
Nb	-1.68	-1.40	1.82
Mo	-1.00	-1.16	2.07
Ru	-0.54	-0.26	2.96
Rh	0.22	1.10	3.27
Pd	1.04	2.85	4.05
Ag	1.43	3.77	4.44
Hf	-2.31	-1.09	1.54
Ta	-2.21	-1.87	1.33
W	-1.62	-1.88	1.42
Re	-0.85	-1.15	2.44

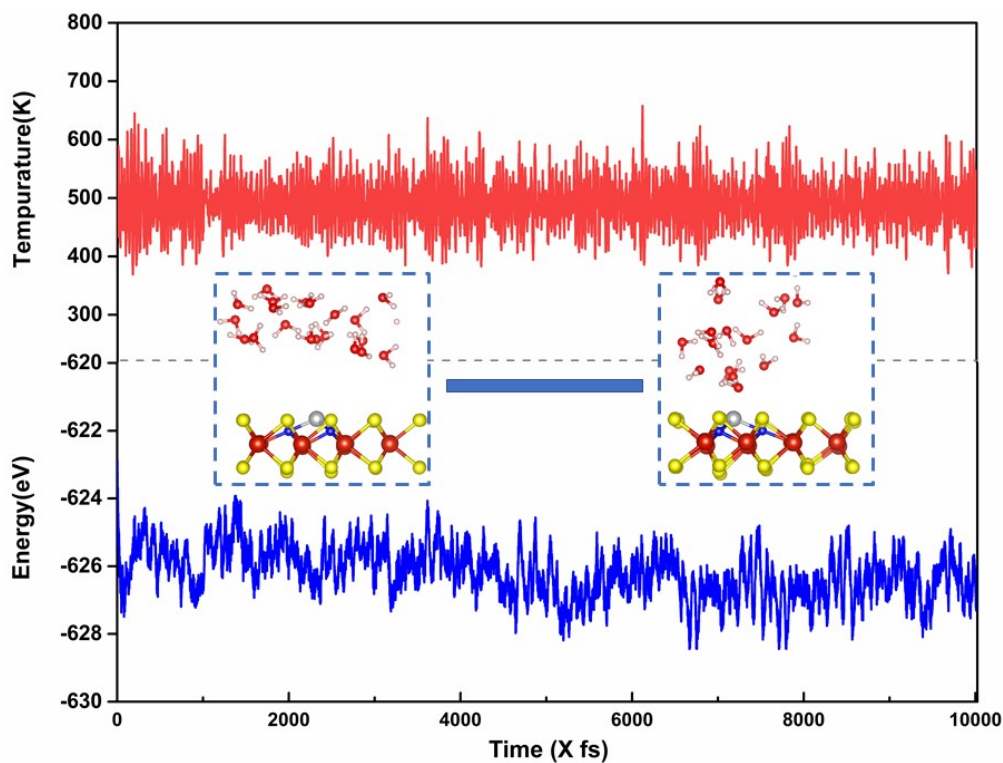
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Os	-0.11	0.00	2.98
Ir	-0.29	0.45	3.05
Pt	0.44	1.65	3.50

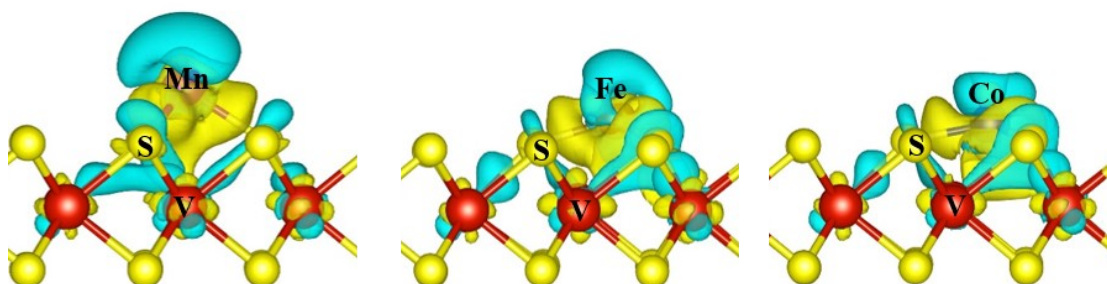
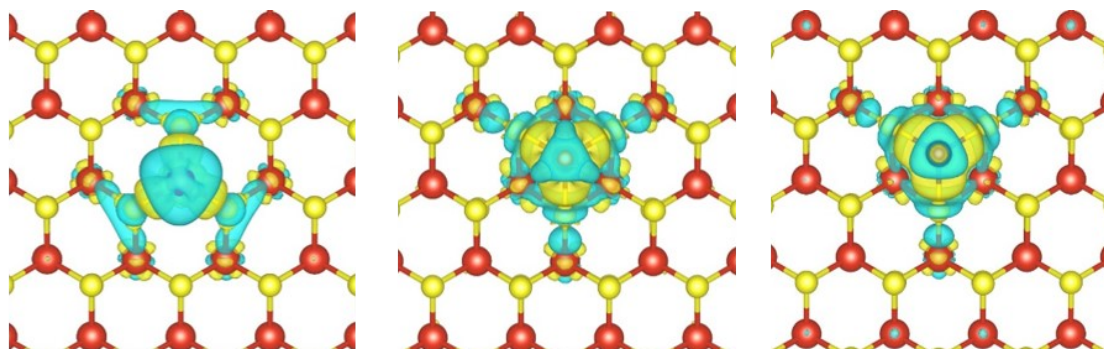
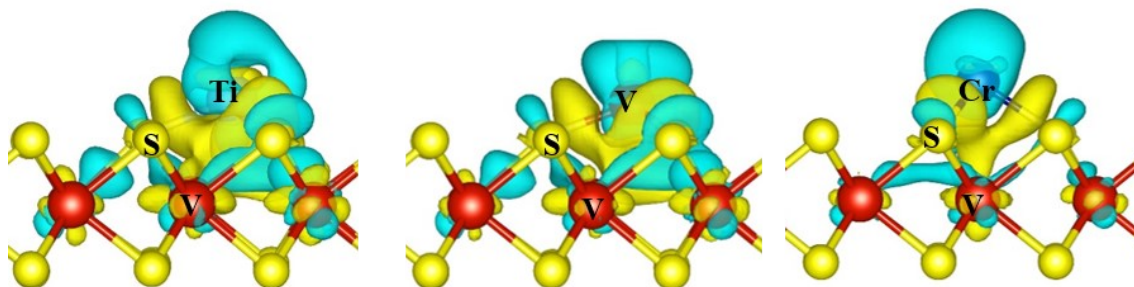
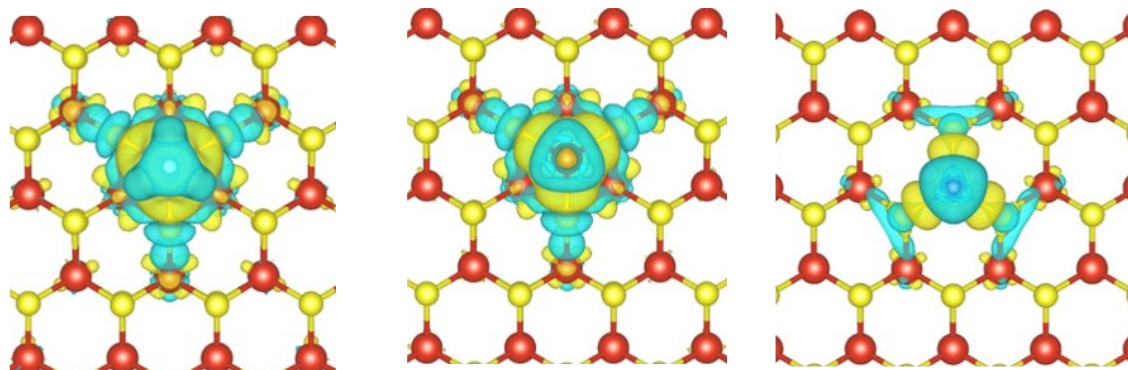
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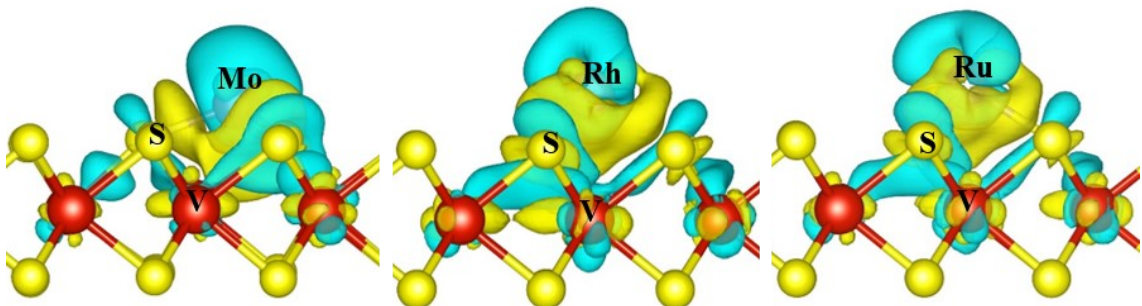
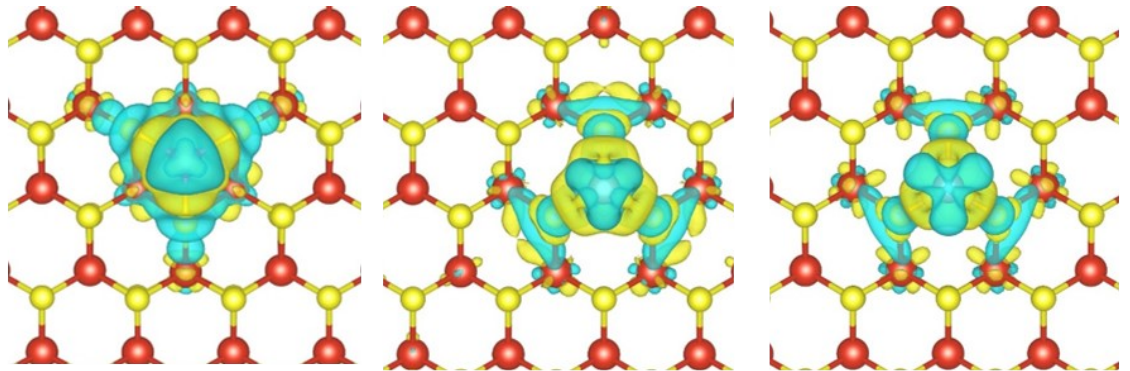
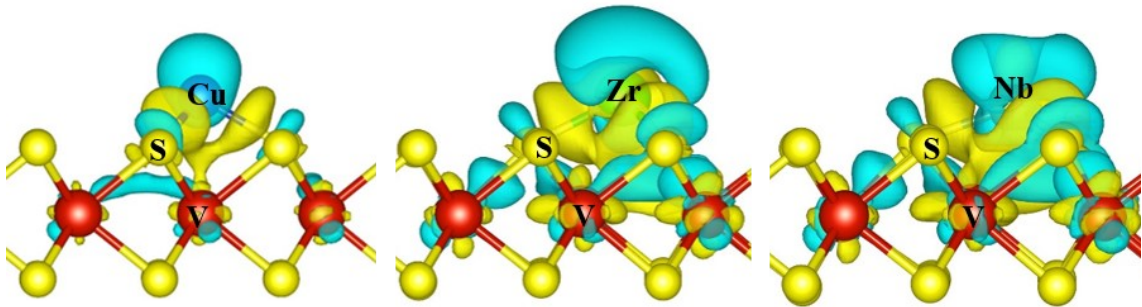
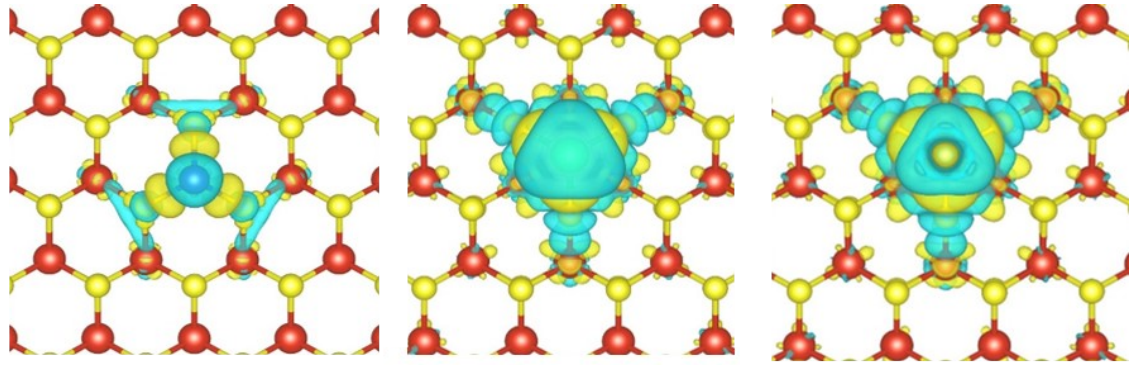


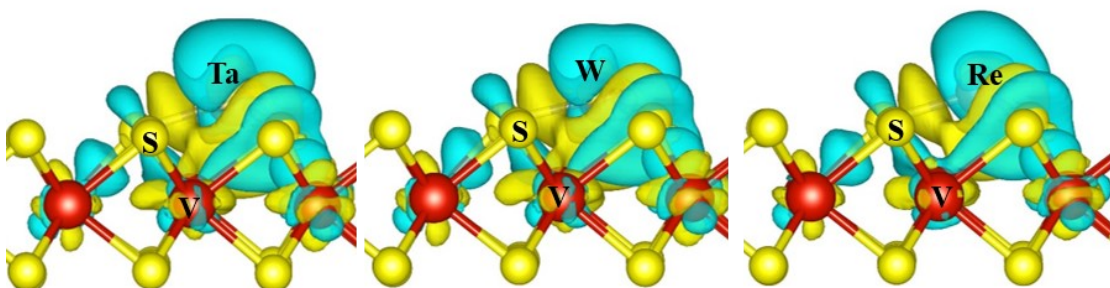
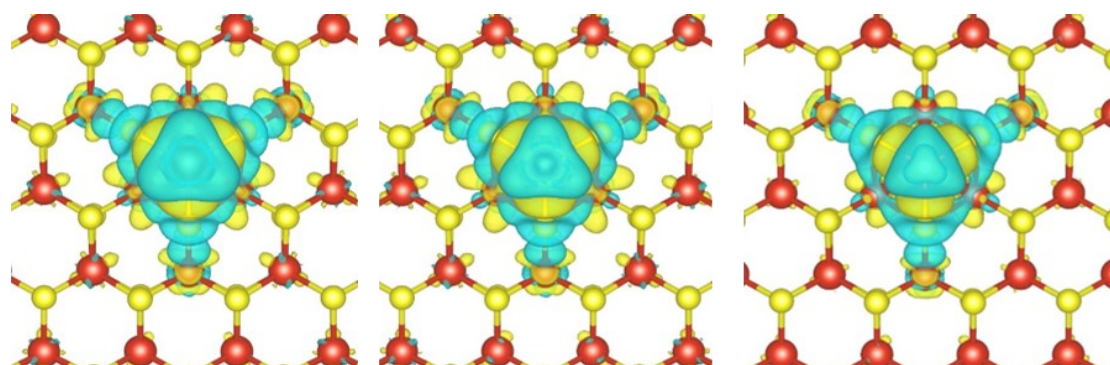
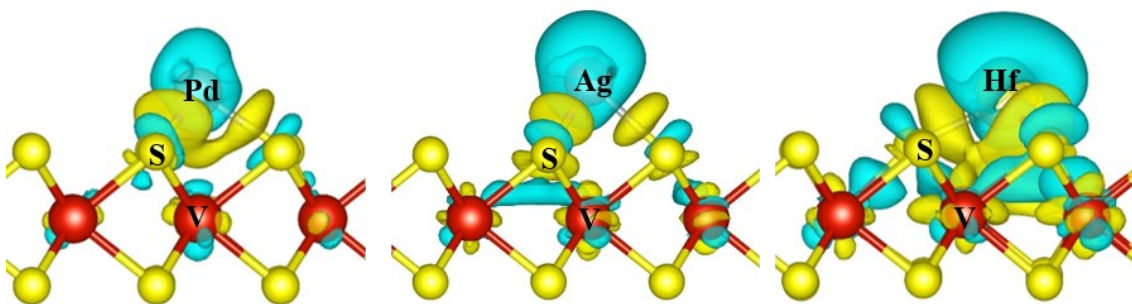
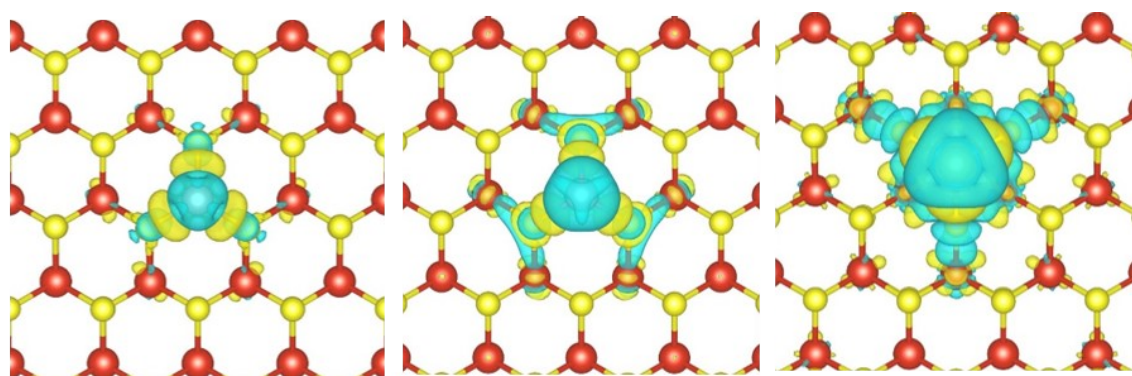
(a)



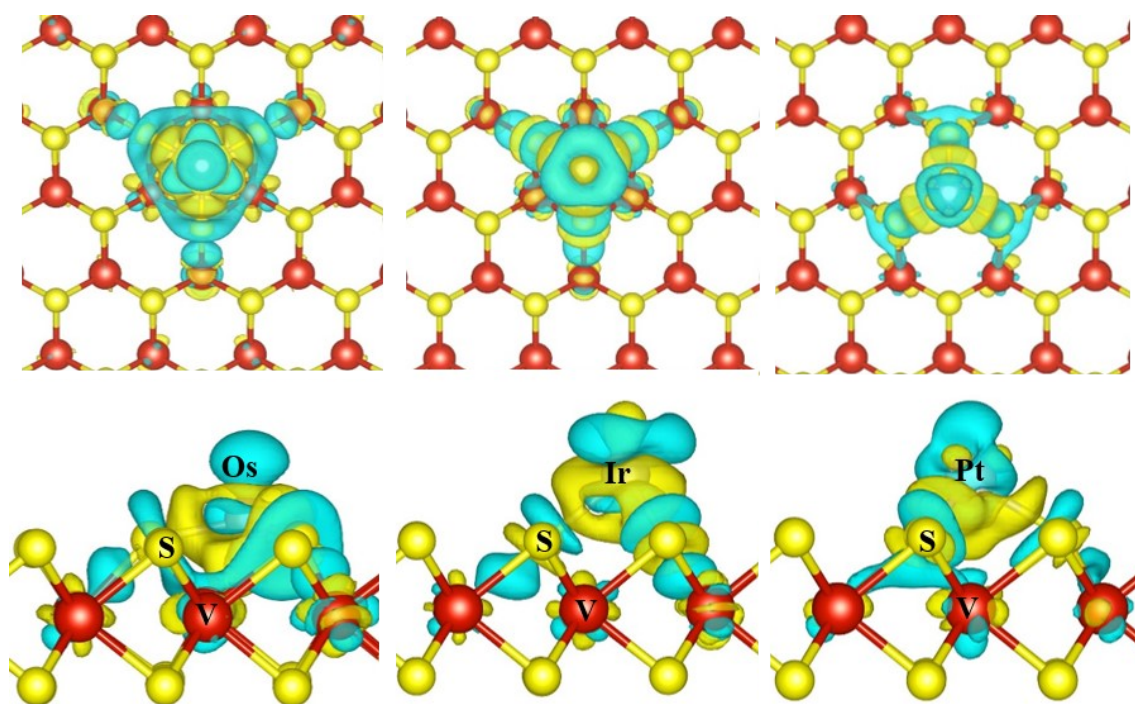
**Fig. S1.** The computed ab initio molecular dynamics (AIMD) simulations at 500 K under the water environments with an overall time scale of 10 ps using the Nosé–Hoover method for (a) Ni@VS<sub>2</sub> and (b) NiN<sub>3</sub>@VS<sub>2</sub> material.





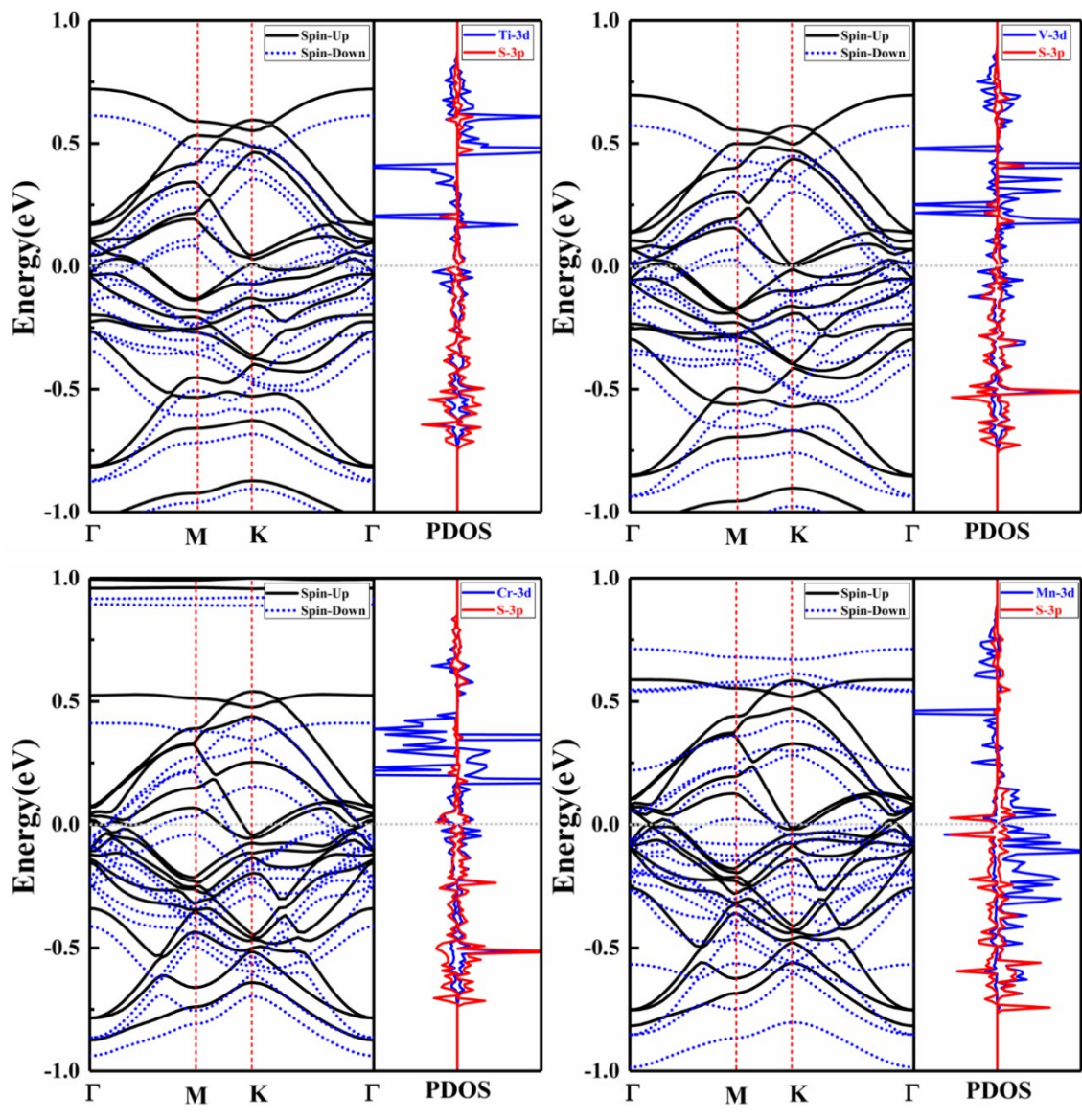


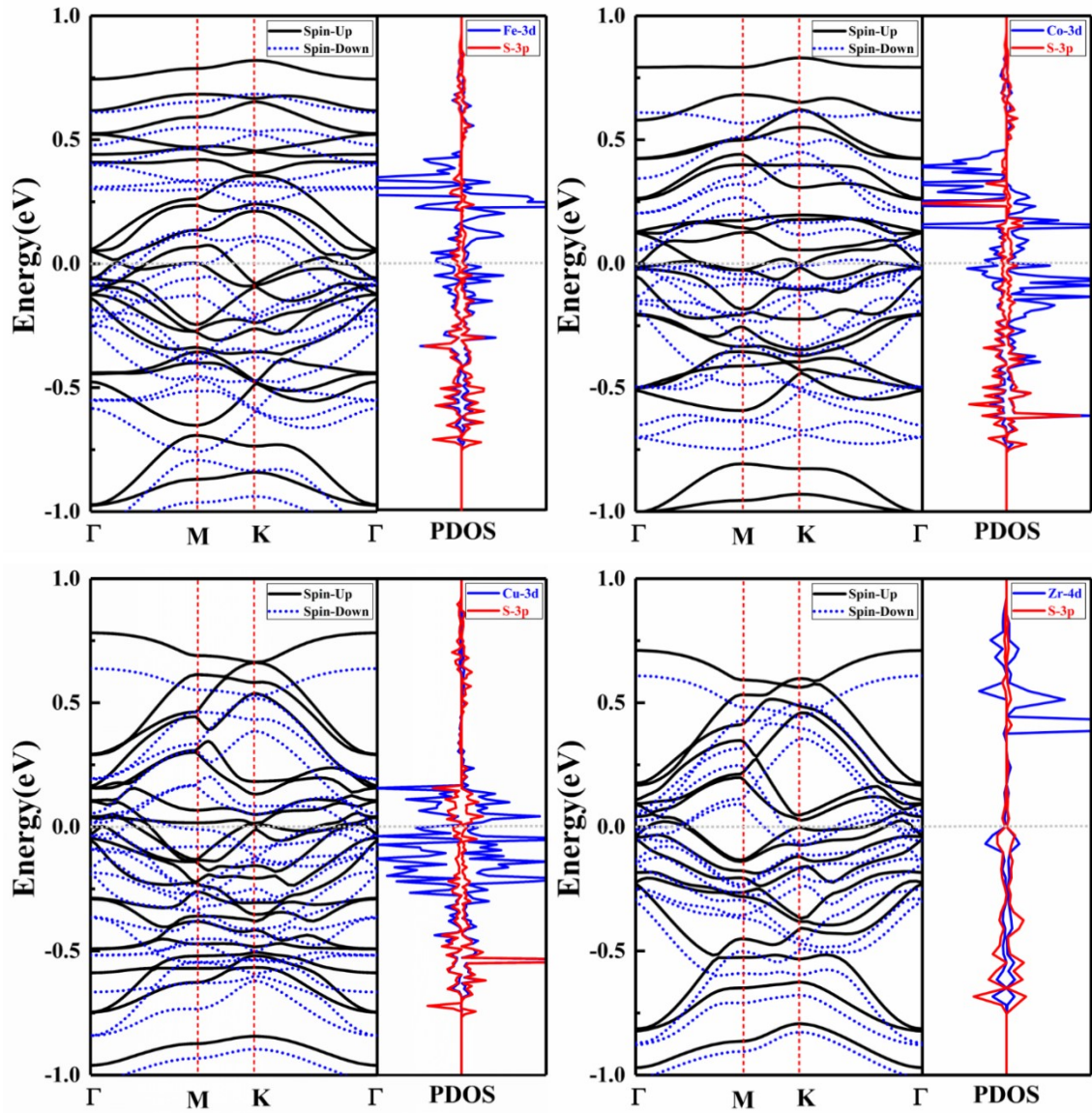


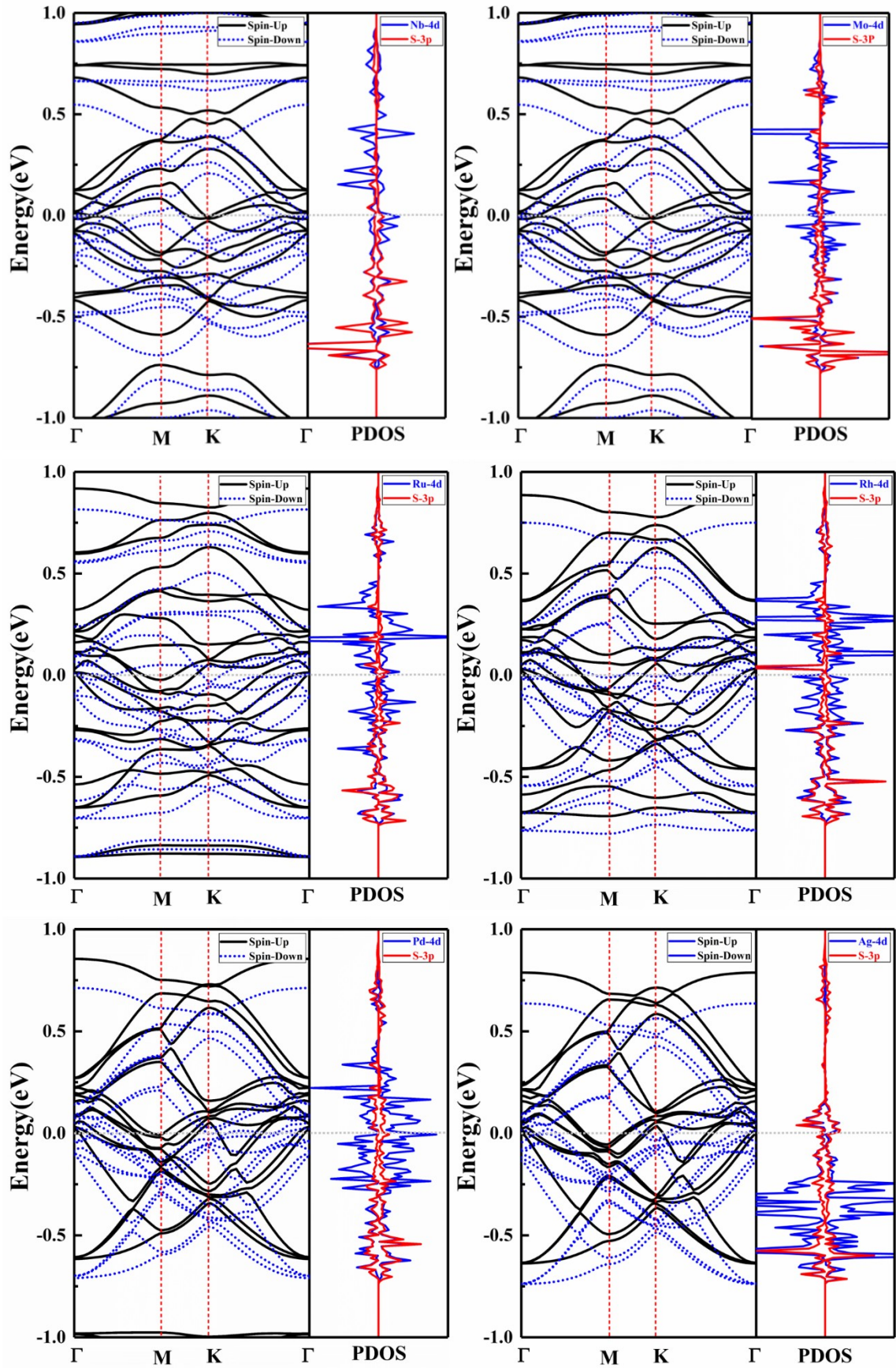


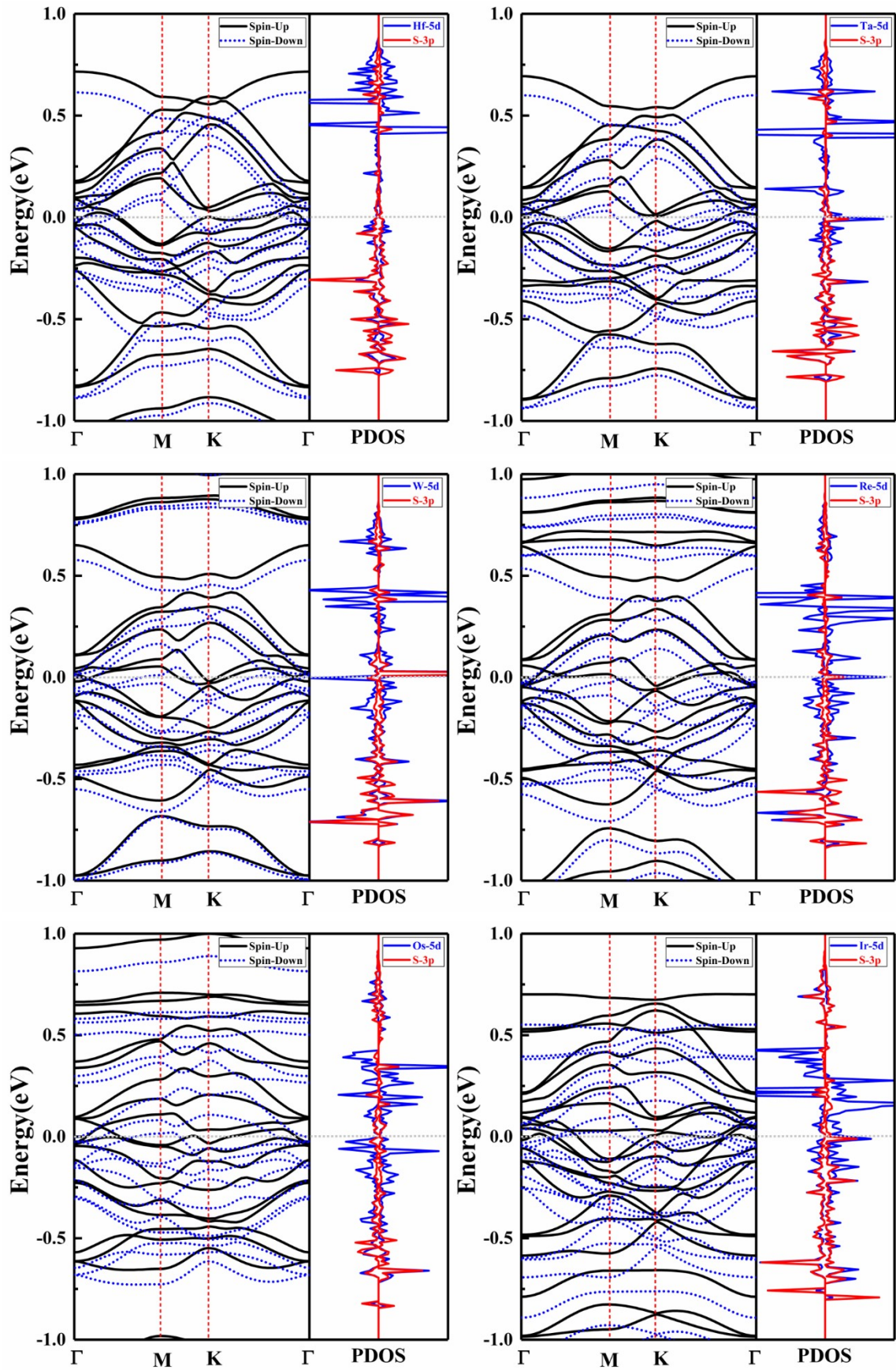
**Fig. S2.** The computed charge density difference of various TM@VS<sub>2</sub> materials.

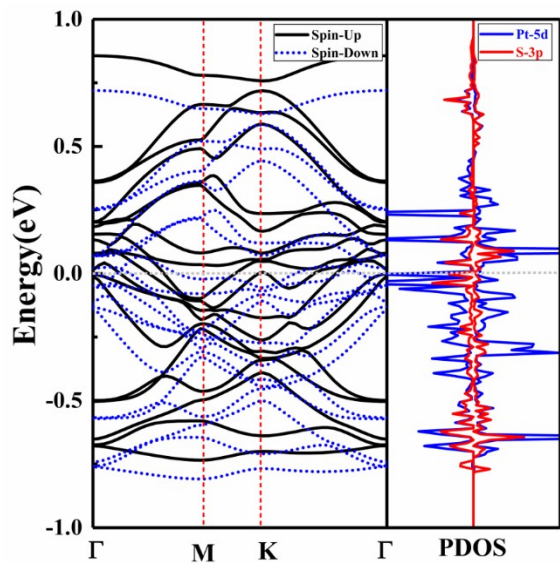
The cyan and yellow areas represent charge depletion and charge accumulation, respectively.



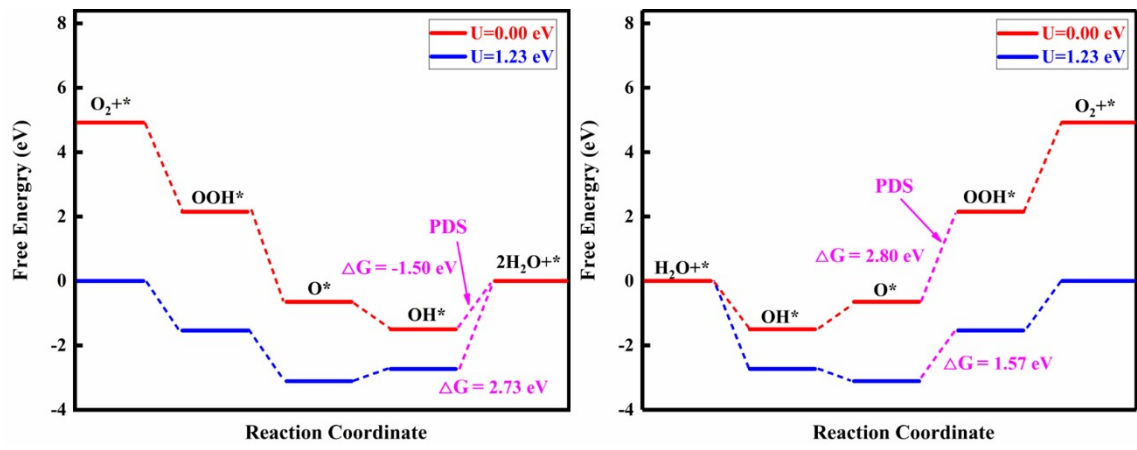




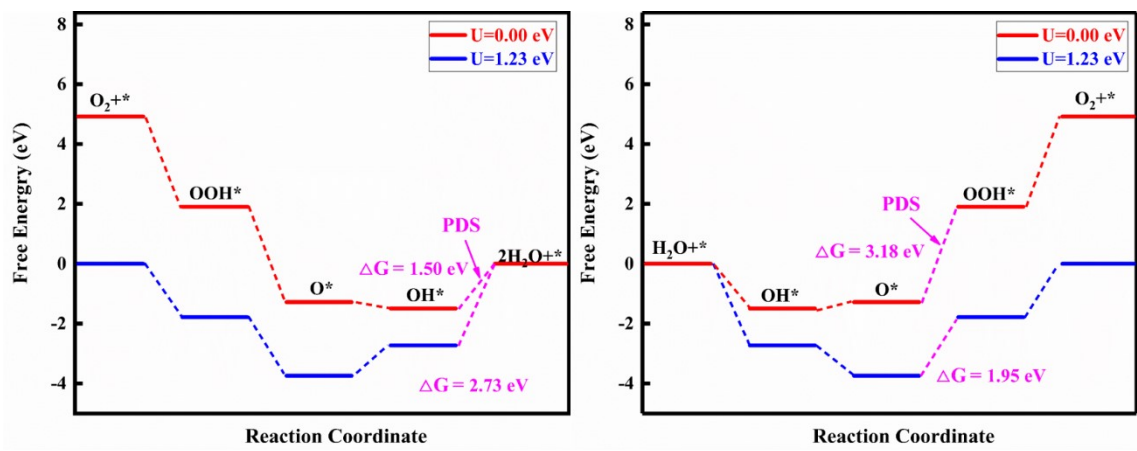




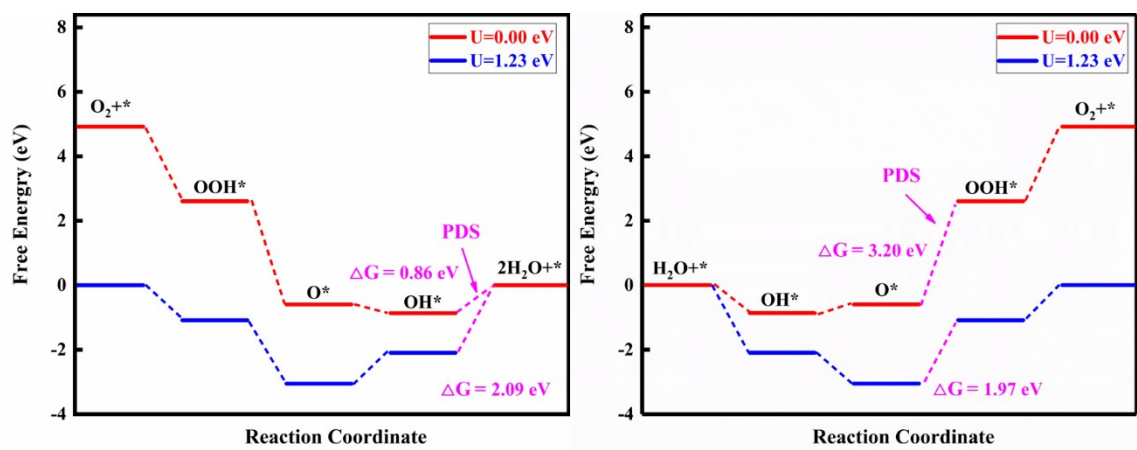
**Fig. S3.** The computed band structures and projected density of states (PDOSs) of various TM/ $\text{VS}_2$  materials. The Fermi level was set to zero.



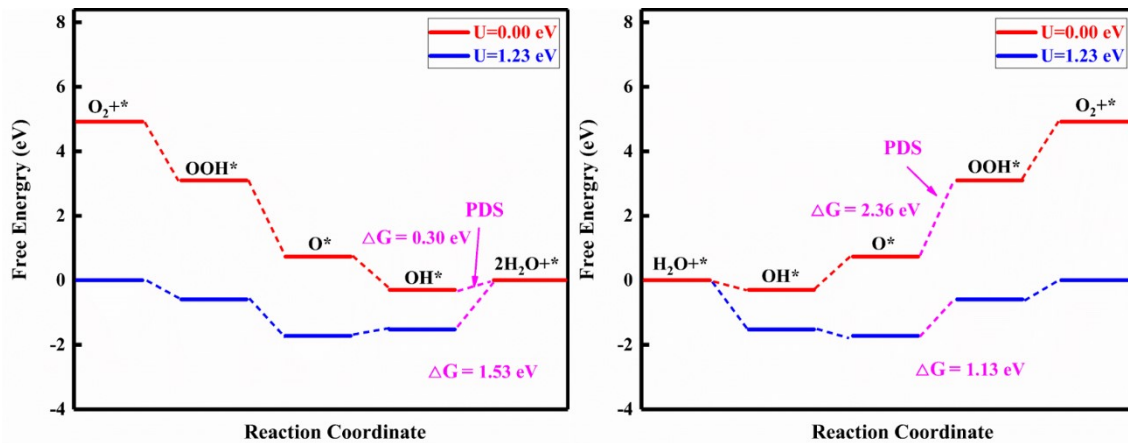
(a)



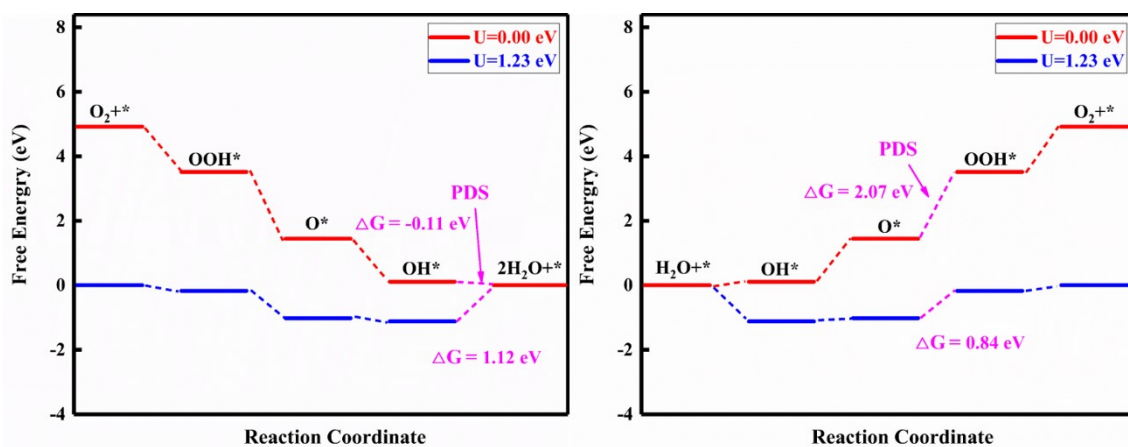
(b)



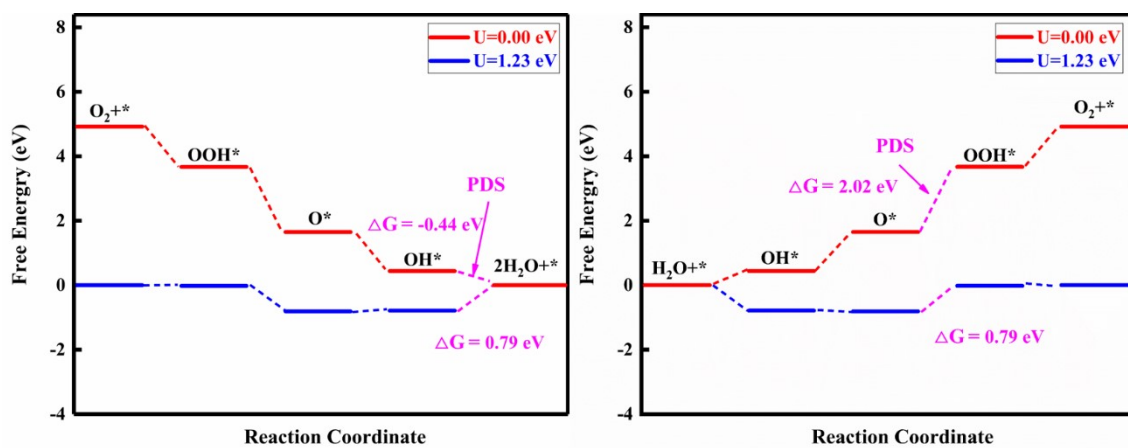
(c)



(d)

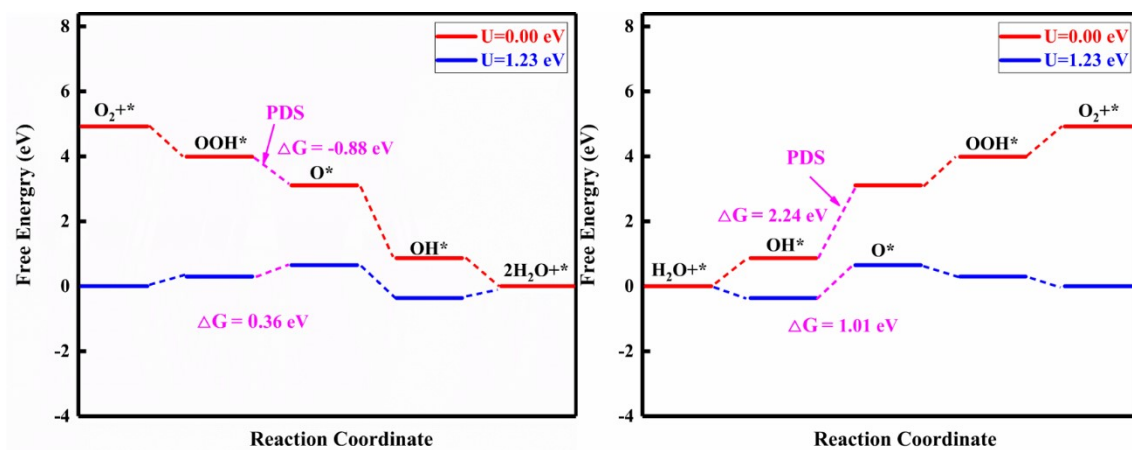


(e)

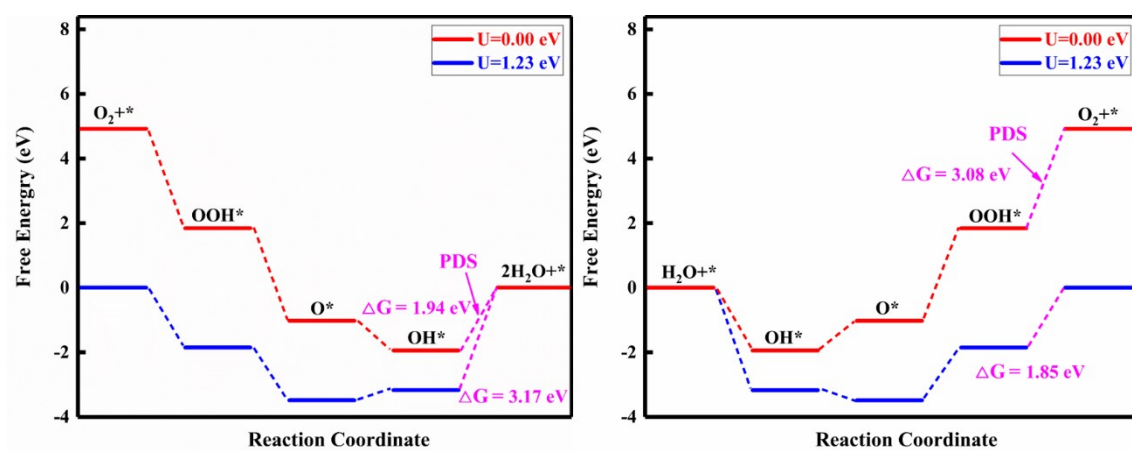


(f)

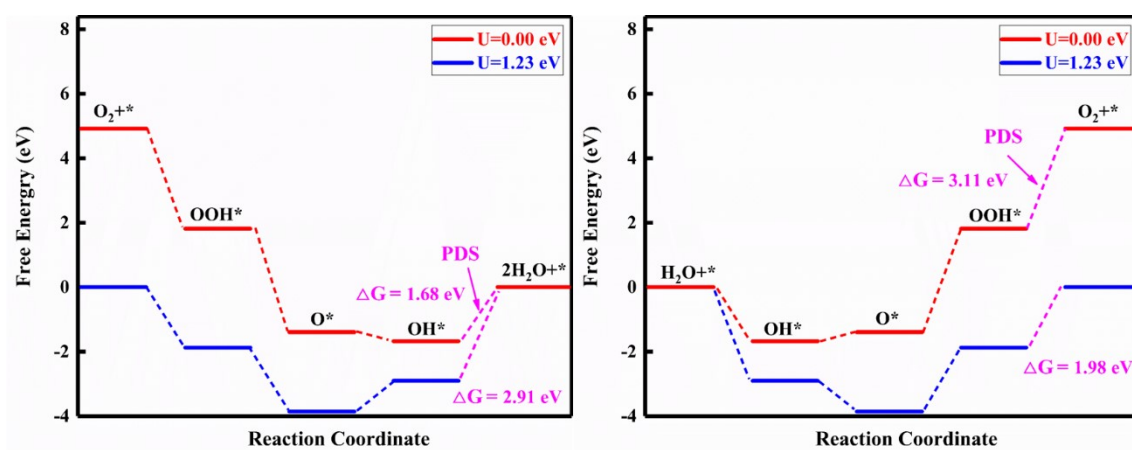




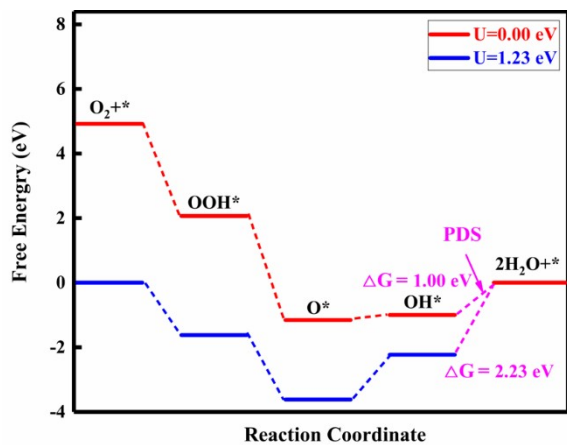
(g)



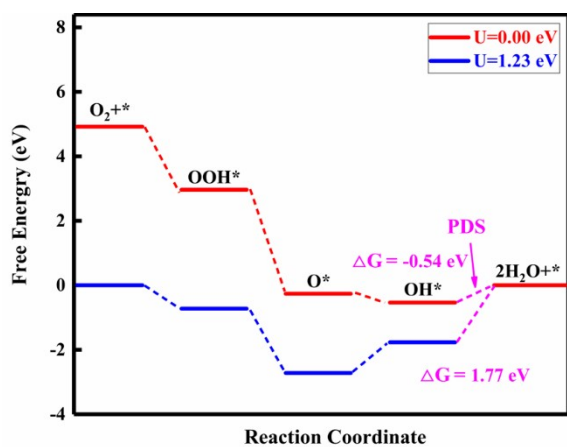
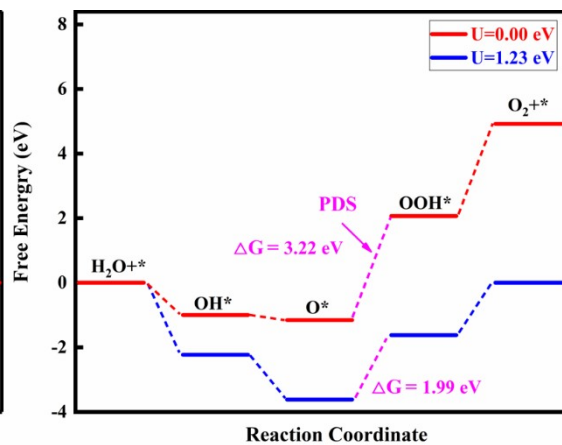
(h)



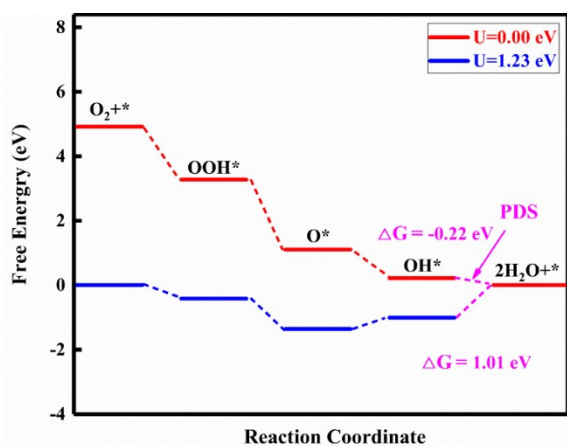
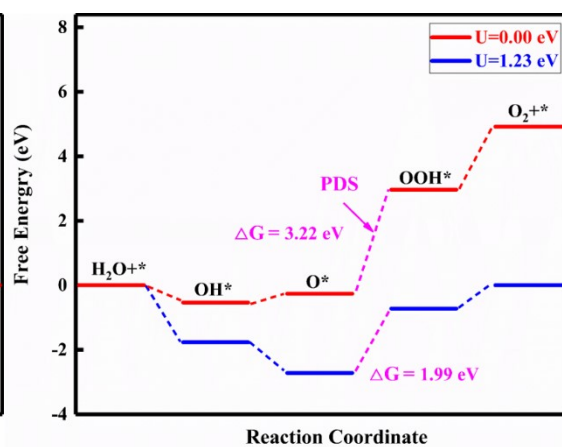
(i)



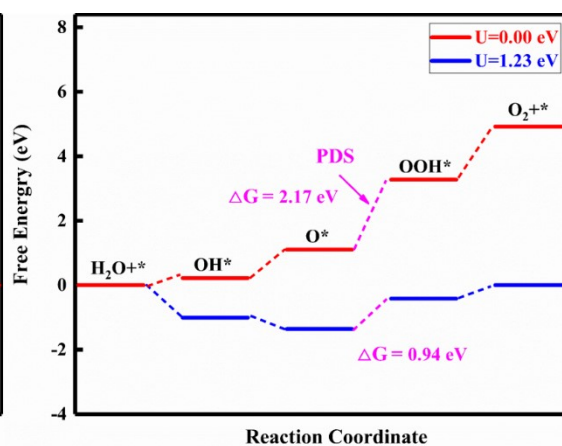
(j)

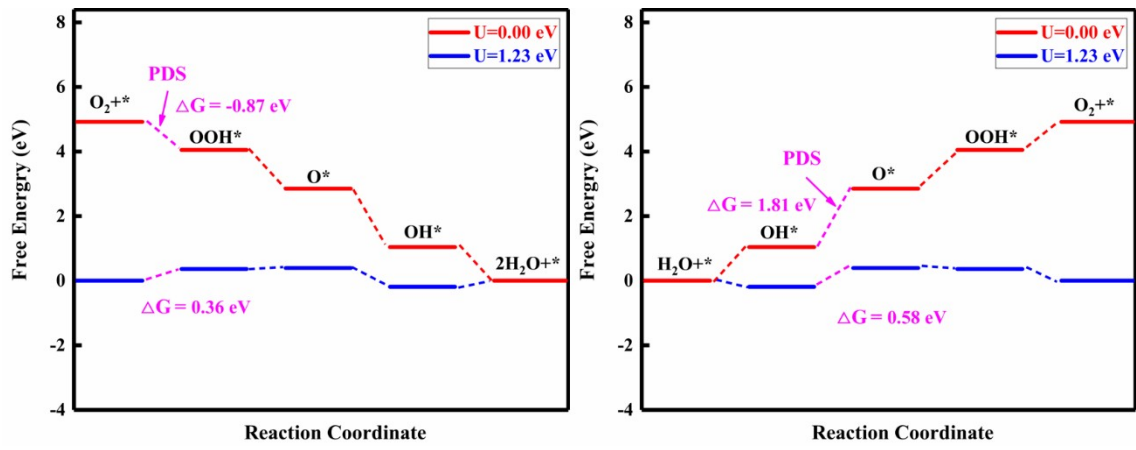


(k)

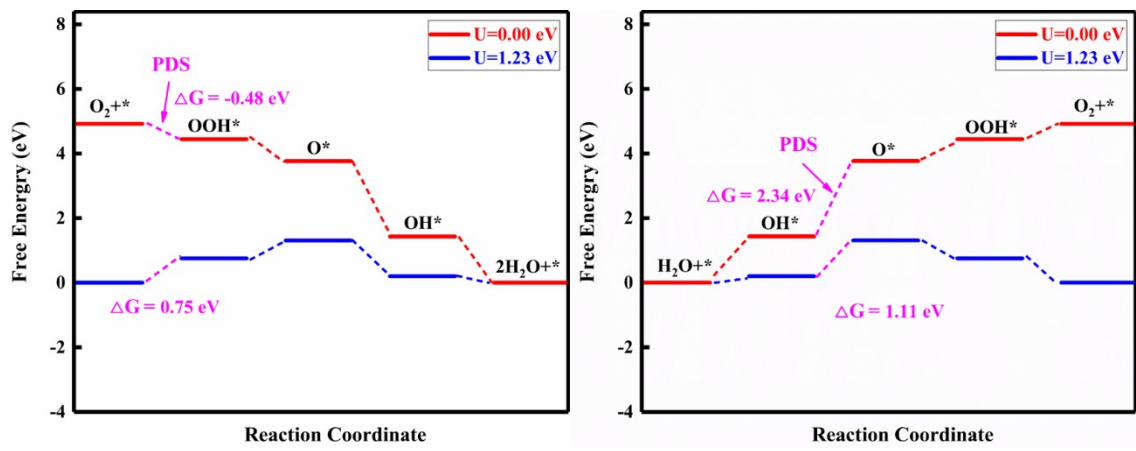


(l)

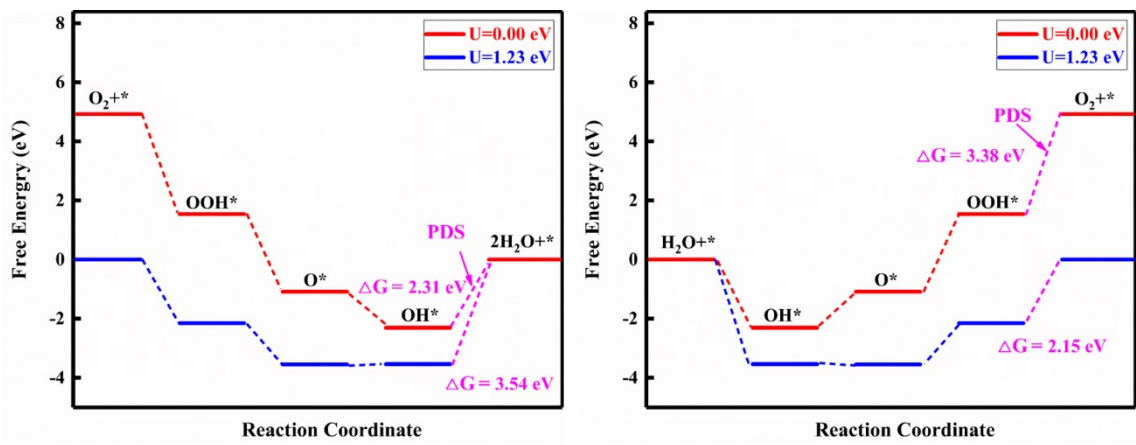




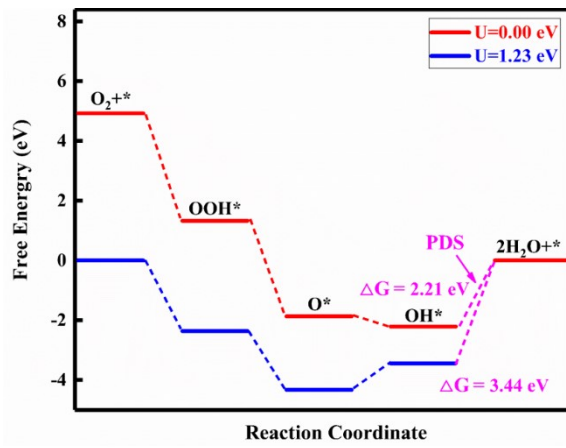
(m)



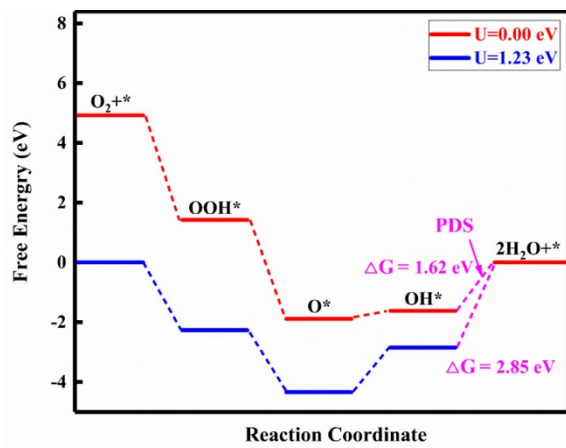
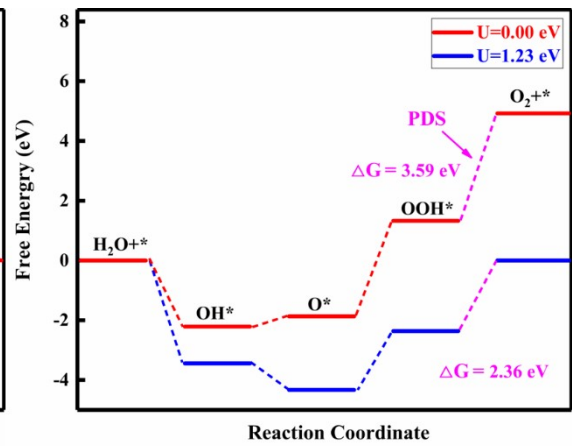
(n)



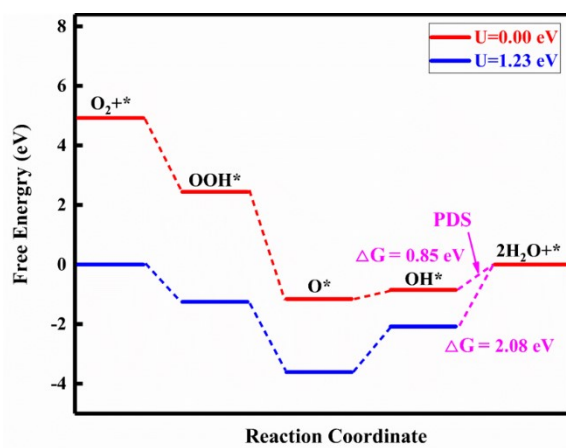
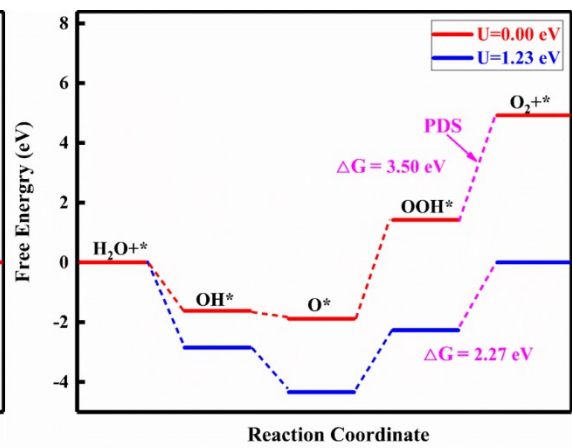
(o)



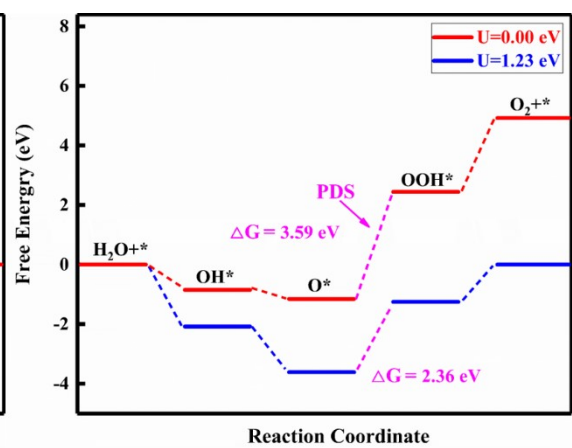
(p)

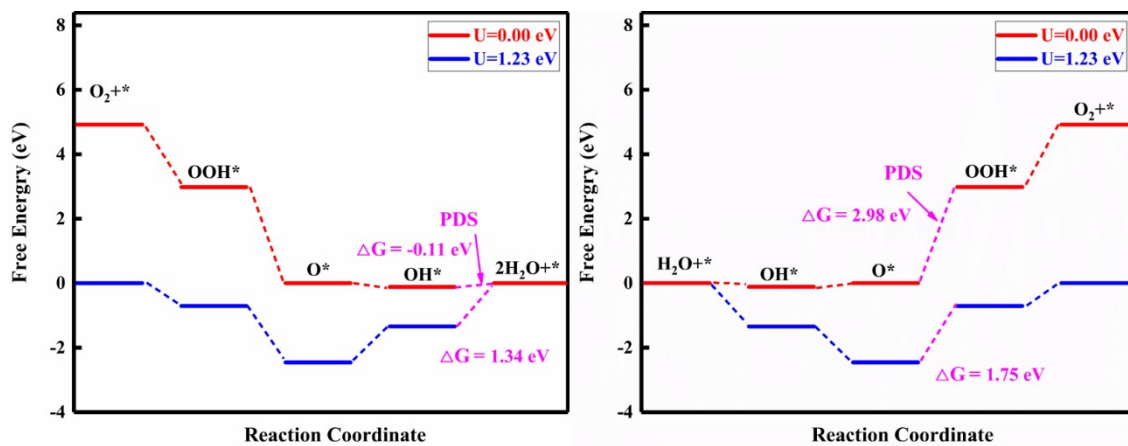


(q)

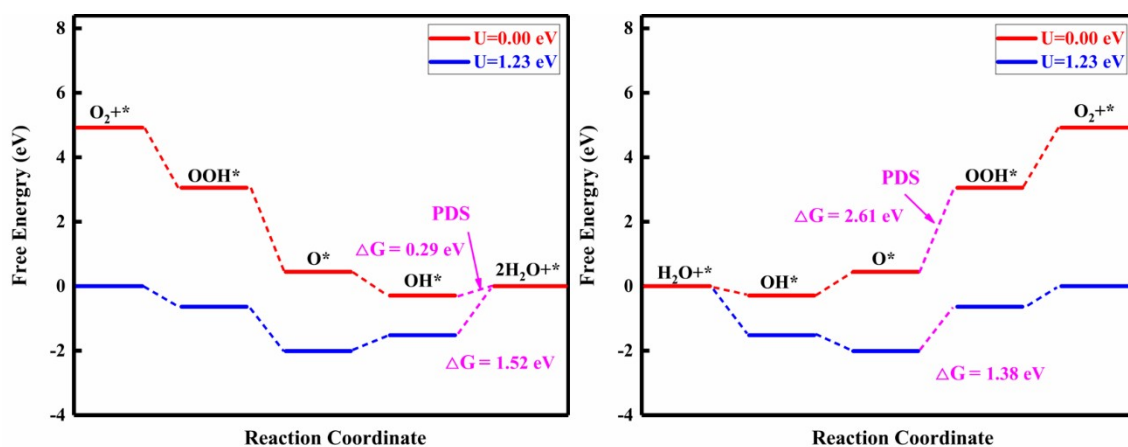


(r)

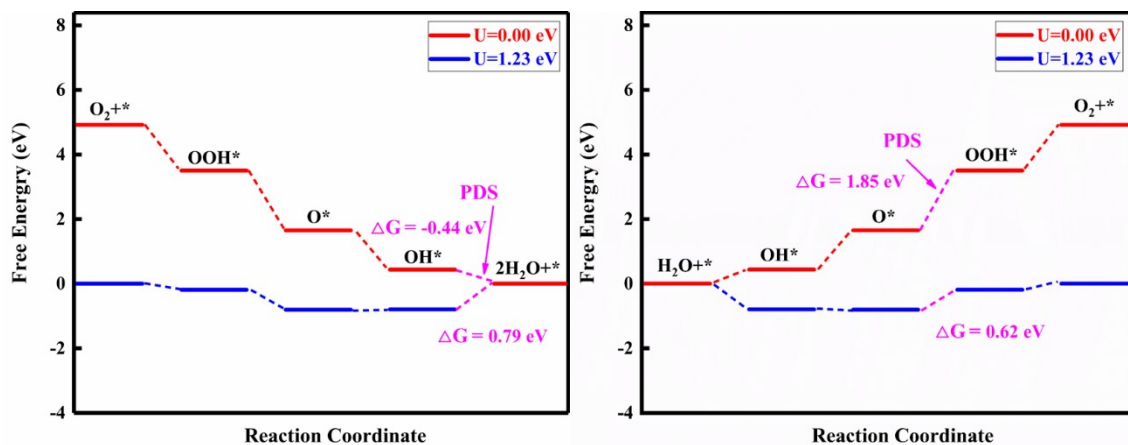




(S)



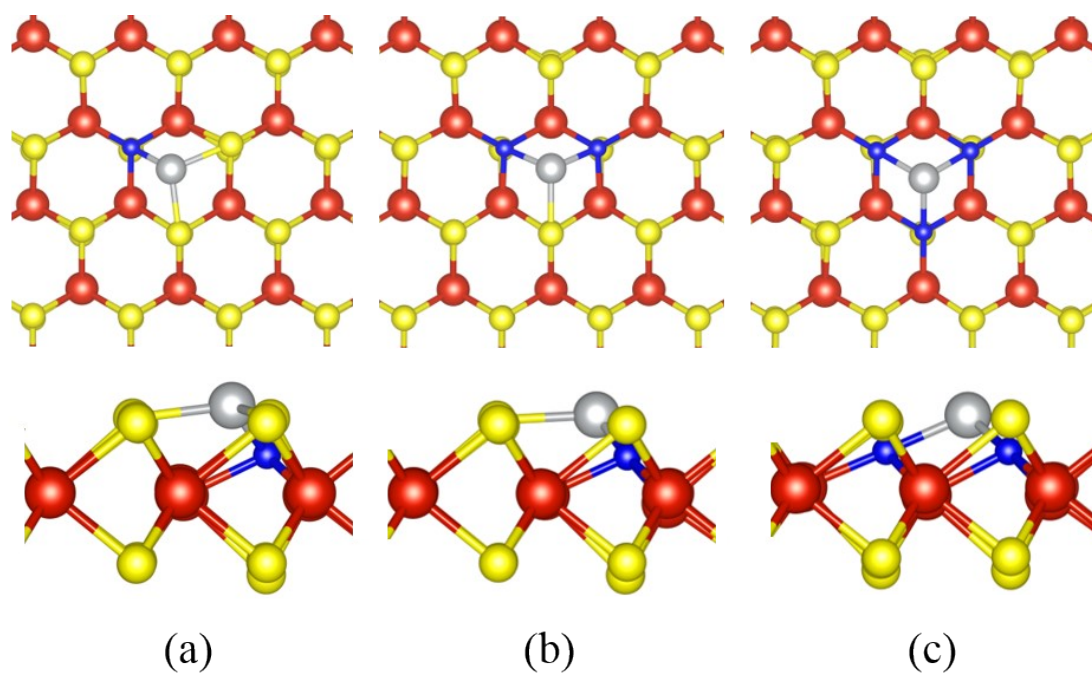
(t)



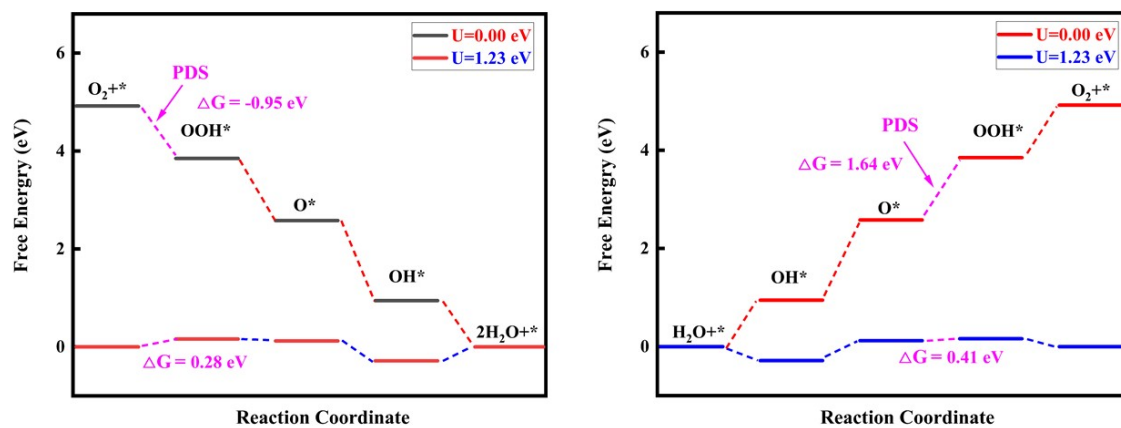
(u)

**Fig. S4.** The computed free energy profiles of ORR (left) and OER (right) on (a) Ti, (b) V, (c) Cr, (d) Mn, (e) Fe, (f) Co, (g) Cu, (h) Zr, (i) Nb, (j) Mo, (k) Ru, (l) Rh, (m)

Pd, (n) Ag, (o) Hf, (p) Ta, (q) W, (r) Re, (s) Os, (t) Ir, and (u) Pt atoms anchored on VS<sub>2</sub> monolayer.



**Fig. S5.** The optimized structures of (a) NiN<sub>1</sub>, (b) NiN<sub>2</sub>, and (c) NiN<sub>3</sub>.



**Fig. S6.** The computed free energy profiles for ORR and OER on  $NiN_3@VS_2$  monolayer with solvent effects.